

High Performance Schottky Rectifier, 1 A



SMA (DO-214AC)



FEATURES

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

PRODUCT SUMMARY	
Package	SMA (DO-214AC)
$I_{F(AV)}$	1 A
V_R	60 V
V_F at I_F	0.63
I_{RM}	7.5 mA at 125 °C
T_J max.	150 °C
Diode variation	Single
E_{AS}	2.0 mJ

DESCRIPTION

The VS-10MQ060NTRPbF surface mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Rectangular waveform	1	A
V_{RRM}		60	V
I_{FSM}	$t_p = 5 \mu s$ sine	40	A
V_F	1.5 A_{pk} , $T_J = 125 \text{ }^\circ\text{C}$	0.63	V
T_J	Range	-55 to +150	°C

VOLTAGE RATINGS			
PARAMETER	SYMBOL	VS-10MQ060NTRPbF	UNITS
Maximum DC reverse voltage	V_R	60	V
Maximum working peak reverse voltage	V_{RWM}		

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current See fig. 4	$I_{F(AV)}$	50 % duty cycle at $T_L = 120 \text{ }^\circ\text{C}$, rectangular waveform On PC board 9 mm ² island (0.013 mm thick copper pad area)	1.5	A
		50 % duty cycle at $T_L = 129 \text{ }^\circ\text{C}$, rectangular waveform On PC board 9 mm ² island (0.013 mm thick copper pad area)	1	
Maximum peak one cycle non-repetitive surge current See fig. 6	I_{FSM}	5 μs sine or 3 μs rect. pulse	40	A
		10 ms sine or 6 ms rect. pulse	10	
Non-repetitive avalanche energy	E_{AS}	$T_J = 25 \text{ }^\circ\text{C}$, $I_{AS} = 1 \text{ A}$, $L = 4 \text{ mH}$	2.0	mJ
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 μs Frequency limited by T_J maximum $V_A = 1.5 \times V_R$ typical	1.0	A



ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop See fig. 1	$V_{FM}^{(1)}$	1 A	$T_J = 25\text{ }^\circ\text{C}$	0.63	V
		1.5 A		0.71	
		1 A	$T_J = 125\text{ }^\circ\text{C}$	0.57	
		1.5 A		0.63	
Maximum reverse leakage current See fig. 2	$I_{RM}^{(1)}$	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_R$	0.5	mA
		$T_J = 125\text{ }^\circ\text{C}$		7.5	
Threshold voltage	$V_{F(TO)}$	$T_J = T_J \text{ maximum}$		0.45	V
Forward slope resistance	r_t			86.8	m Ω
Typical junction capacitance	C_T	$V_R = 10\text{ V}_{DC}$, $T_J = 25\text{ }^\circ\text{C}$, test signal = 1 MHz		31	pF
Typical series inductance	L_S	Measured lead to lead 5 mm from package body		2.0	nH
Maximum voltage rate of change	dV/dt	Rated V_R		10 000	V/ μ s

Note(1) Pulse width < 300 μ s, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	$T_J^{(1)}$, T_{Stg}			-55 to +150	$^\circ\text{C}$
Maximum thermal resistance, junction to ambient	R_{thJA}	DC operation		80	$^\circ\text{C/W}$
Approximate weight				0.07	g
				0.002	oz.
Marking device		Case style SMA (DO-214AC) (similar D-64)		1H	

Note(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink

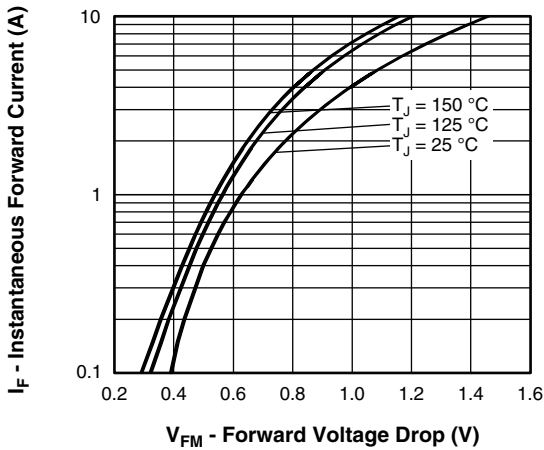


Fig. 1 - Maximum Forward Voltage Drop Characteristics

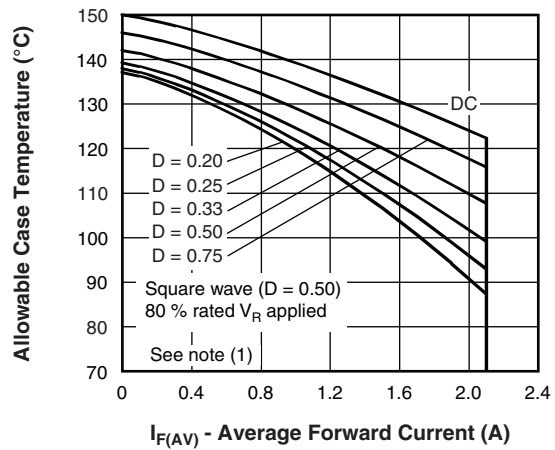


Fig. 4 - Maximum Average Forward Current vs. Allowable Lead Temperature

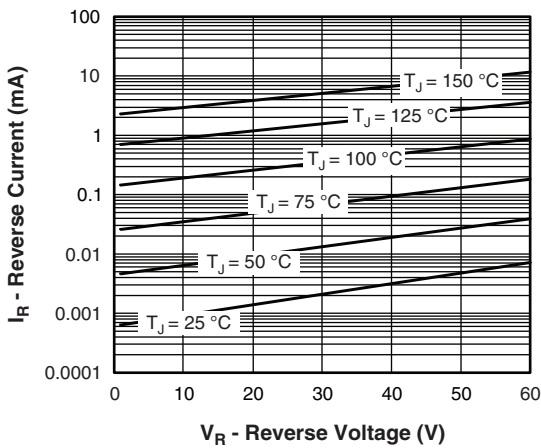


Fig. 2 - Typical Peak Reverse Current vs. Reverse Voltage

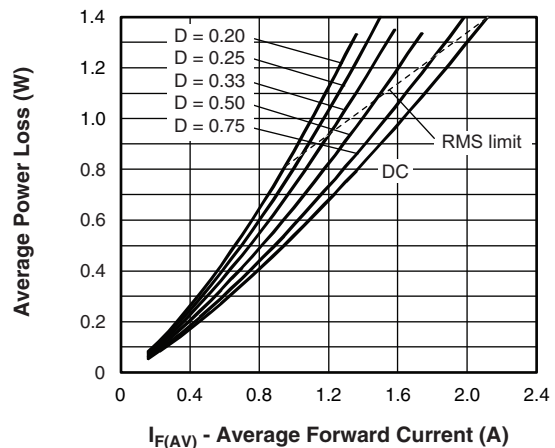


Fig. 5 - Maximum Average Forward Dissipation vs. Average Forward Current

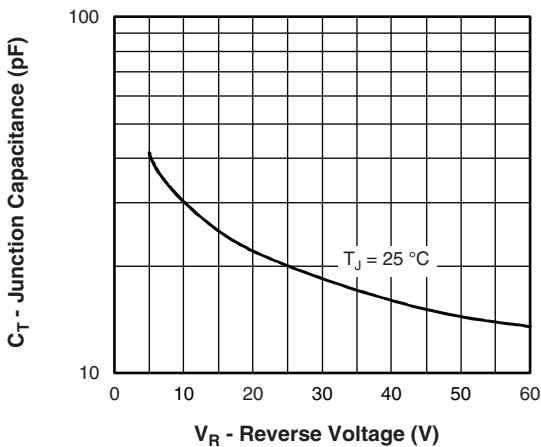


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

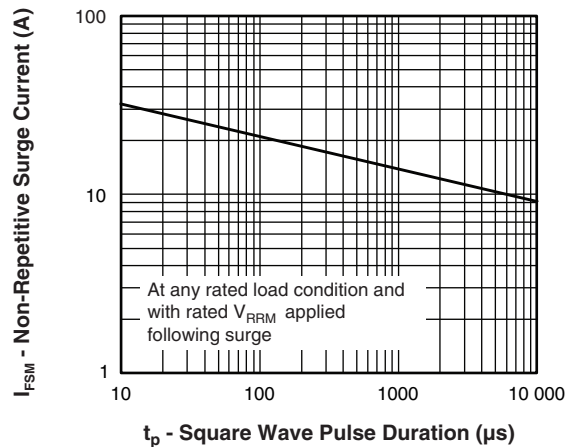


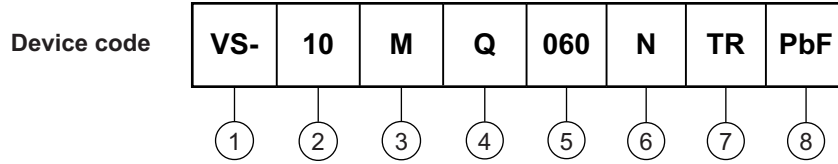
Fig. 6 - Maximum Peak Surge Forward Current vs. Pulse Duration

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$;
- P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
- $P_{d_{REV}}$ = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80\%$ rated V_R



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Current rating (10 = 1 A)
- 3** - M = SMA
- 4** - Q = Schottky "Q" series
- 5** - Voltage rating (060 = 60 V)
- 6** - N = new SMA
- 7** - TR = tape and reel
- 8** - PbF = lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	PREFERRED PACKAGE CODE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-10MQ060NTRPbF	5AT	7500	13" diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95400
Part marking information	www.vishay.com/doc?95403
Packaging information	www.vishay.com/doc?95404

SMA

DIMENSIONS in inches (millimeters)

